

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,838,391 B2
DATED : January 4, 2005
INVENTOR(S) : Volker Harle

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited, OTHER PUBLICATIONS**,

“B. Henle,” reference, replace “*On Indium Phosphide & Rel. Materials, U.S. NY; IEEE, Bd.*” with -- *On Indium Phosphide & Rel. Materials, U.S. NY IEEE, Bd.* --
J.P. Harbinson et al.,” reference, replace “*J.P. Harbinson et al., “Tungsten Patterning As A Technique”* with -- *J.P. Harbinson et al., “Tungsten Patterning As A Technique* --
“JP 02-046407”, reference, replace “*JP 02-046407, Patent Abstracts of Japan, Veroffentlicung:*” with -- *JP 02-046407, Patent Abstracts of Japan, Veroffentlicung:* --
“Whidden T.K. et al.” reference, replace “*Whidden T.K. et al.; “Catalyzed HF Vapor Etching Of”* with -- *Whidden T.K. et al.; “Catalyzed HF Vapor Etching Of* --
“Wong M. et al.” reference, replace “*Oxide And Oxide Etching Using Vapor-Phase Hydrgoen*” with -- *Oxide And Oxide Etching Using Vapor-Phase Hydrogen* --

Column 5.

Line 29, replace “more from a group consisting of an underlying mask layer” with
-- or more from a group consisting of an underlying mask layer --

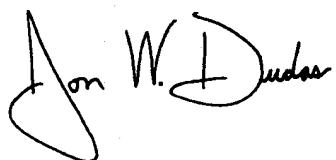
Line 51, replace “defined an at least one (N+1)th semiconductor compo-” with
-- defined and at least one (N+1)th semiconductor-compo- --

Column 6.

Line 29, replace “any remaining mask is moved by etching.” with -- any remaining
mask is removed by etching. --

Signed and Sealed this

Twenty-fourth Day of May, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office